

## INCHANGE SEMICONDUCTOR

## **Isc N-Channel MOSFET Transistor**

## SPA07N60CFD

### FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

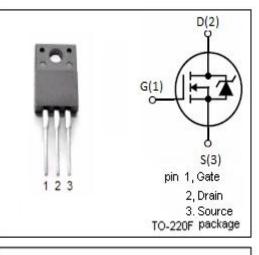
Switching applications

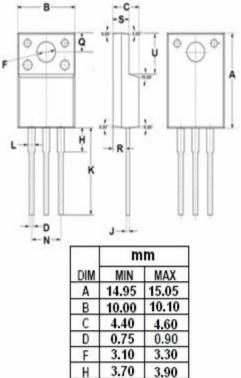
ADSOLUTE MAXIMUM (ATHOS(Ta-23 C)						
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	600	V			
V <sub>GSS</sub>	Gate-Source Voltage	±30	V			
ID	Drain Current-Continuous @Tc=25℃   (V <sub>GS</sub> at 10V) Tc=100℃	6.6 4.3	A			
I <sub>DM</sub>	Drain Current-Single Pulsed	17	A			
PD	Total Dissipation @Tc=25°C	32	W			
Tj	Max. Operating Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			

### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	3.9	°C <b>/W</b>	
Rth(ch-a)	(ch-a) Channel-to-ambient thermal resistance		°C/W	





J

K

L

Ν

Q

R

5

0.50

13.4

1.10

5.00

2.70

2.20

6.40

0.70

13.6

1.30

5.20

2.90

2.40

2.90

6.60

# isc website: www.iscsemi.cn

## isc & iscsemi is registered trademark



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	600			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.3mA	3.0		5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =4.6A		590	700	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V;Tj=25℃ V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; Tj=150℃			1 100	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =6.6A, V <sub>GS</sub> = 0 V		1.0	1.2	V



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